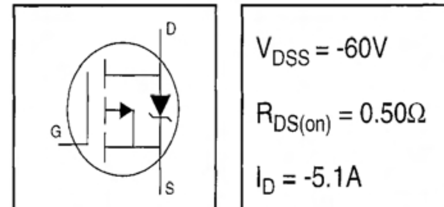
International
IOR Rectifier
HEXFET® Power MOSFET

PD- 95383A

IRFR9014PbF
IRFU9014PbF

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Surface Mount (IRFR9014)
- Straight Lead (IRFU9014)
- Available in Tape & Reel
- P-Channel
- Fast Switching
- **Lead-Free**



V_{DSS} = -60V

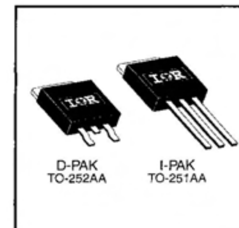
$R_{DS(on)}$ = 0.50Ω

I_D = -5.1A

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ -10 V	-5.1	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ -10 V	-3.2	
I_{DM}	Pulsed Drain Current ①	-20	
P_D @ T_C = 25°C	Power Dissipation	25	W
P_D @ T_A = 25°C	Power Dissipation (PCB Mount)**	2.5	
	Linear Derating Factor	0.20	W/°C
	Linear Derating Factor (PCB Mount)**	0.020	
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	140	mJ
I_{AR}	Avalanche Current ①	-5.1	A
E_{AR}	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-4.5	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	260 (1.6mm from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	5.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

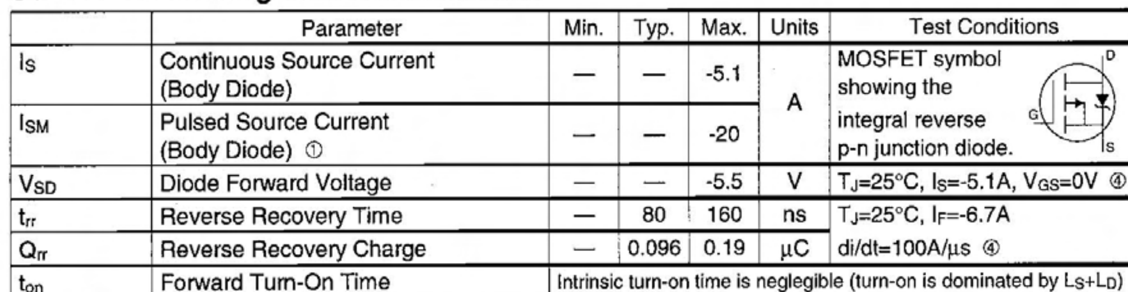
** When mounted on 1" square PCB (FR-4 or G-10 Material).

Downloaded from Elcodis.com electronic components distributor

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-60	—	—	V	V_{GS}=0V, I_D=-250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.059	—	V/°C	Reference to 25°C, I_D=-1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.50	Ω	V_{GS}=-10V, I_D=-3.1A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	V_{DS}=V_{GS}, I_D=-250μA
g_{fs}	Forward Transconductance	1.4	—	—	S	V_{DS}=-25V, I_D=-3.1A ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	-100	μA	V_{DS}=-60V, V_{GS}=0V
		—	—	-500		V_{DS}=-48V, V_{GS}=0V, T_J=125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS}=-20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS}=20V
Q_g	Total Gate Charge	—	—	12	nC	I_D=-6.7A
Q_{gs}	Gate-to-Source Charge	—	—	3.8		V_{DS}=-48V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	5.1		V_{GS}=-10V See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	V_{DD}=-30V
t_r	Rise Time	—	63	—		I_D=-6.7A
$t_{d(off)}$	Turn-Off Delay Time	—	9.6	—		R_G=24Ω
t_f	Fall Time	—	31	—		R_D=4.0Ω See Figure 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	270	—	pF	V_{GS}=0V
C_{oss}	Output Capacitance	—	170	—		V_{DS}=-25V
C_{rss}	Reverse Transfer Capacitance	—	31	—		f=1.0MHz See Figure 5

Source-Drain Ratings and Characteristics



	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-5.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-20		
V_{SD}	Diode Forward Voltage	—	—	-5.5	V	T_J=25°C, I_S=-5.1A, V_{GS}=0V ④
t_{rr}	Reverse Recovery Time	—	80	160	ns	T_J=25°C, I_F=-6.7A
Q_{rr}	Reverse Recovery Charge	—	0.096	0.19	μC	di/dt=100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is neglegible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

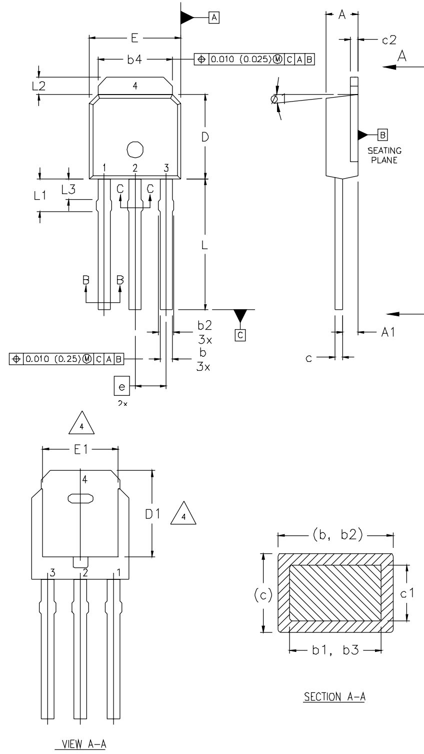
② V_{DD}=-25V, starting T_J=25°C, L=6.3mH R_G=25Ω, I_{AS}=-5.1A (See Figure 12)

③ I_{SD}≤-6.7A, di/dt≤90A/μs, V_{DD}≤$V_{(BR)DSS}$, T_J≤150°C

④ Pulse width ≤ 300 μs; duty cycle ≤2%.

Downloaded from Elcodis.com electronic components distributor

I-Pak (TO-251AA) Package Out (line Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
5. LEAD DIMENSION UNCONTROLLED IN L3.
6. DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
7. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
8. CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0°	15°	0°	15°	

LEAD ASSIGNMENTS

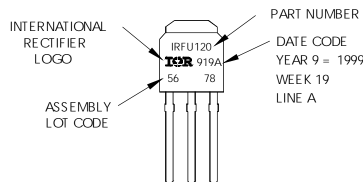
HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

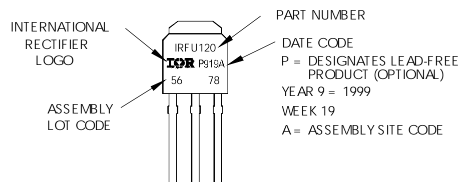
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"



OR



Downloaded from Elcodis.com electronic components distributor